PTO/SB/08A	Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	10/039,196
	Filing Date	January 2, 2002
(use as many sheets as necessary)	Confirmation Number	7221
	First Named Inventor	Robert J. Falster
	Group Art Unit	1765
	Examiner Name	
Sheet 1 of 2	Attorney Docket No.	MEMC 00-1400 (2806.1)

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
	1	5,919,302		Falster et al.	07-06-1999
	2	5,994,761		Falster et al.	11-30-1999
	3	6,180,220		Falster et al.	01-30-2001
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	7	6,336,968		Falster	01-08-2002

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[4]
	8	R. FALSTER "The Phenomenology of Dielectric Breakdown in Thin Silicon Dioxide Films: Al Cathodes and p-type Si Anodes" J. Appl. Phys., Vol. 66, No. 7 (1989) pp. 3355-3370.	
	9	R. FALSTER et al. "On the Properties of the Intrinsic Point Defects in Silicon: A Perspective from Crystal Growth and Wafer Processing" Phys. Stat. Sol. (b), Vol. 222, No. 1 (2000) pp. 219-244.	

Examiner Signature		Date Considered	3/24/04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Unique citation designation number. [2] See attached Kinds of U.S. Patent Documents. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached or place an "A" here if English language abstract is attached.

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